

Excellent Integrated System Limited

Stocking Distributor

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[IXYS Corporation](#)
[FUO50-16N](#)

For any questions, you can email us directly:

sales@integrated-circuit.com

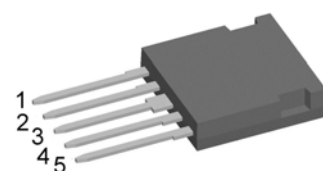
Standard Rectifier

3~ Rectifier	
V_{RRM}	= 1600 V
I_{DAV}	= 50 A
I_{FSM}	= 270 A

3~ Rectifier Bridge

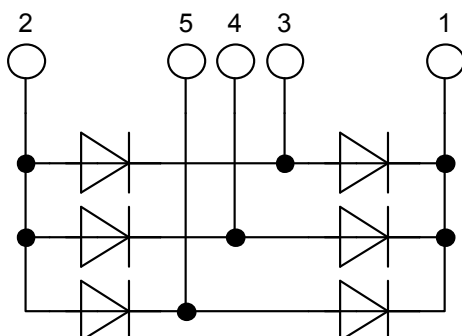
Part number

FOU50-16N



Backside: isolated

E72873



Features / Advantages:

- Package with DCB ceramic
- Reduced weight
- Improved temperature and power cycling
- Planar passivated chips
- Very low forward voltage drop
- Very low leakage current

Applications:

- Diode for main rectification
- For single and three phase bridge configurations

Package: i4-Pac

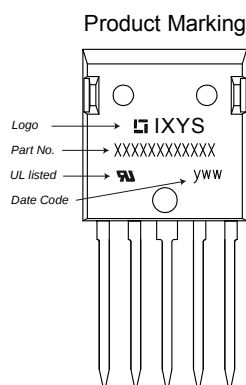
- Isolation Voltage: 3000V~
- Industry convenient outline
- RoHS compliant
- Epoxy meets UL 94V-0
- Soldering pins for PCB mounting
- Backside: DCB ceramic
- Reduced weight
- Advanced power cycling

Rectifier				Ratings			
Symbol	Definition	Conditions		min.	typ.	max.	Unit
V _{RSM}	max. non-repetitive reverse blocking voltage	T _{VJ} = 25°C				1700	V
V _{RRM}	max. repetitive reverse blocking voltage	T _{VJ} = 25°C				1600	V
I _R	reverse current, drain current	V _R = 1600 V	T _{VJ} = 25°C			20	μA
		V _R = 1600 V	T _{VJ} = 150°C			1	mA
V _F	forward voltage drop	I _F = 15 A	T _{VJ} = 25°C			1.15	V
		I _F = 45 A				1.50	V
		I _F = 15 A	T _{VJ} = 150 °C			1.04	V
		I _F = 45 A				1.55	V
I _{DAV}	bridge output current	T _C = 120°C rectangular d = ⅓	T _{VJ} = 175°C			50	A
V _{F0}	threshold voltage	} for power loss calculation only		T _{VJ} = 175°C		0.78	V
r _F	slope resistance					17	mΩ
R _{thJC}	thermal resistance junction to case					2.1	K/W
R _{thCH}	thermal resistance case to heatsink				0.20		K/W
P _{tot}	total power dissipation	T _C = 25°C				70	W
I _{FSM}	max. forward surge current	t = 10 ms; (50 Hz), sine	T _{VJ} = 45°C			270	A
		t = 8,3 ms; (60 Hz), sine	V _R = 0 V			290	A
		t = 10 ms; (50 Hz), sine	T _{VJ} = 150°C			230	A
		t = 8,3 ms; (60 Hz), sine	V _R = 0 V			250	A
I ² t	value for fusing	t = 10 ms; (50 Hz), sine	T _{VJ} = 45°C			365	A²s
		t = 8,3 ms; (60 Hz), sine	V _R = 0 V			350	A²s
		t = 10 ms; (50 Hz), sine	T _{VJ} = 150°C			265	A²s
		t = 8,3 ms; (60 Hz), sine	V _R = 0 V			260	A²s
C _J	junction capacitance	V _R = 400 V; f = 1 MHz		T _{VJ} = 25°C		8	pF



FUO50-16N

Package i4-Pac			Ratings			
Symbol	Definition	Conditions	min.	typ.	max.	Unit
I_{RMS}	RMS current	per terminal			50	A
T_{stg}	storage temperature		-55		150	°C
T_{VJ}	virtual junction temperature		-55		175	°C
Weight				9		g
F_C	mounting force with clip		20		120	N
$d_{Spp/App}$	creepage distance on surface striking distance through air	terminal to terminal	1.7			mm
$d_{Spb/Apb}$		terminal to backside	5.1			mm
V_{ISOL}	isolation voltage	t = 1 second	3000			V
		t = 1 minute 50/60 Hz, RMS; $I_{ISOL} \leq 1$ mA	2500			V



Ordering	Part Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	FUO50-16N	FUO50-16N	Tube	25	498637

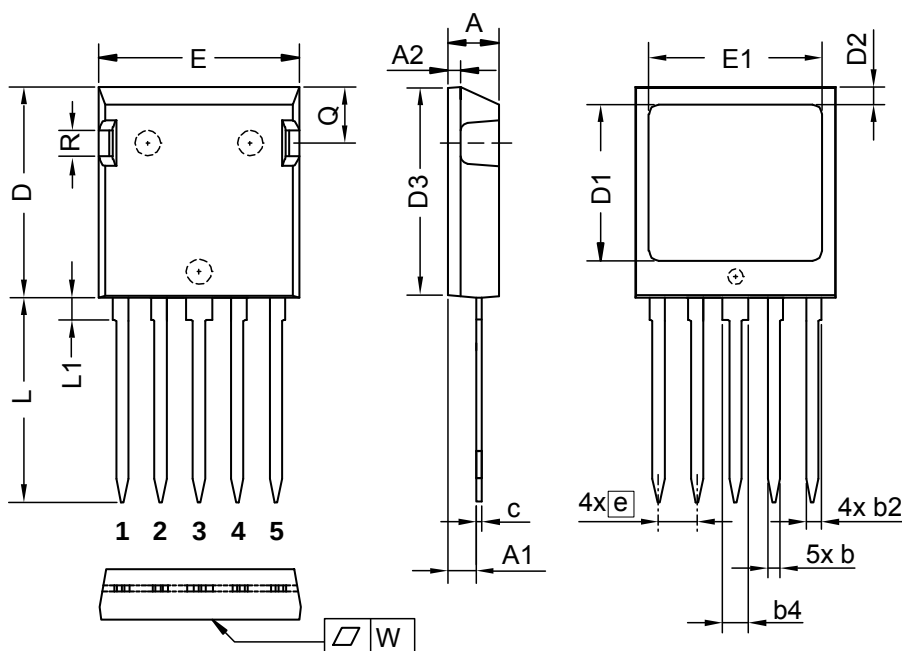
Equivalent Circuits for Simulation

* on die level

$T_{VJ} = 175^{\circ}\text{C}$

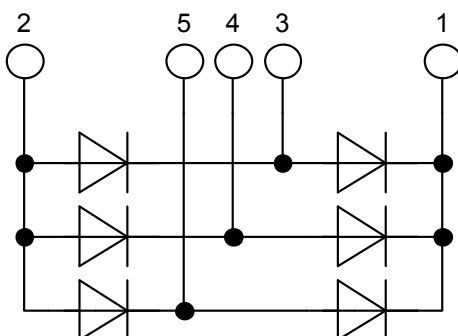
		Rectifier	
$V_{0\max}$	threshold voltage	0.78	V
$R_{0\max}$	slope resistance *	14	mΩ

Outlines i4-Pac



Dim.	Millimeter		Inches	
	min	max	min	max
A	4.83	5.21	0.190	0.205
A1	2.59	3.00	0.102	0.118
A2	1.17	2.16	0.046	0.085
b	1.14	1.40	0.045	0.055
b2	1.47	1.73	0.058	0.068
b4	2.54	2.79	0.100	0.110
c	0.51	0.74	0.020	0.029
D	20.80	21.34	0.819	0.840
D1	14.99	15.75	0.590	0.620
D2	1.65	2.03	0.065	0.080
D3	20.30	20.70	0.799	0.815
E	19.56	20.29	0.770	0.799
E1	16.76	17.53	0.660	0.690
e	3.81 BSC		0.150 BSC	
L	19.81	21.34	0.780	0.840
L1	2.11	2.59	0.083	0.102
Q	5.33	6.20	0.210	0.244
R	2.54	4.57	0.100	0.180
W	-	0.10	-	0.004

Die konvexe Form des Substrates ist typ. < 0.05 mm über der Kunststoffoberfläche der Bauteilunterseite
The convex bow of substrate is typ. < 0.05 mm over plastic surface level of device bottom side



Rectifier

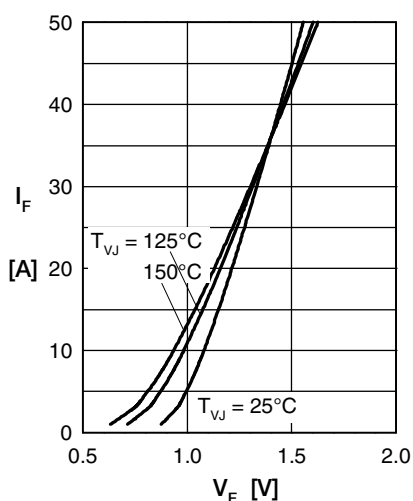


Fig. 1 Forward current versus voltage drop per diode

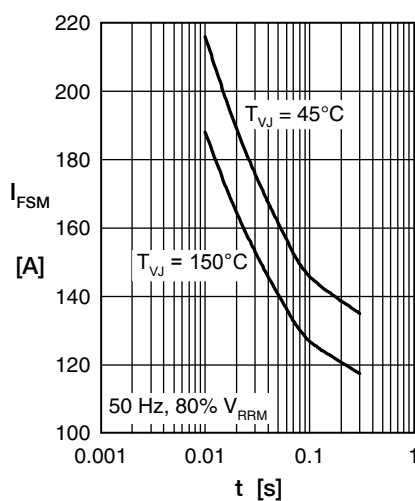


Fig. 2 Surge overload current

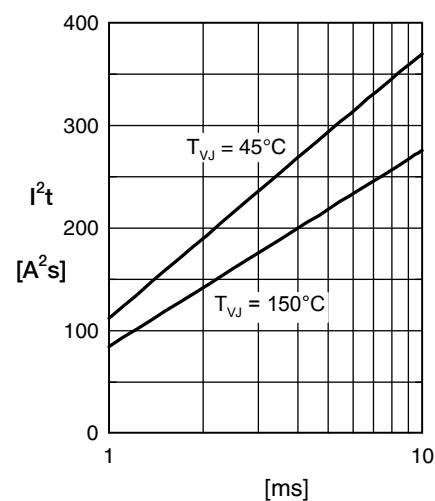


Fig. 3 I^2t versus time per diode

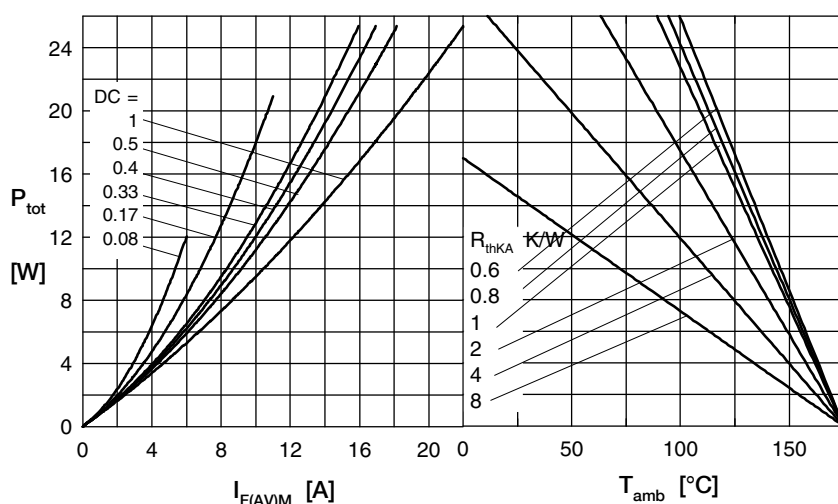


Fig. 4 Power dissipation vs. direct output current & ambient temperature

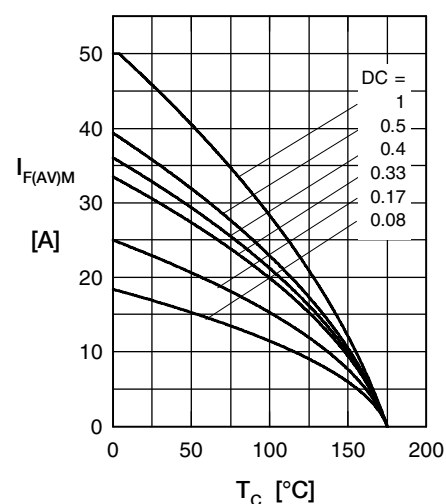


Fig. 5 Max. forward current vs. case temperature

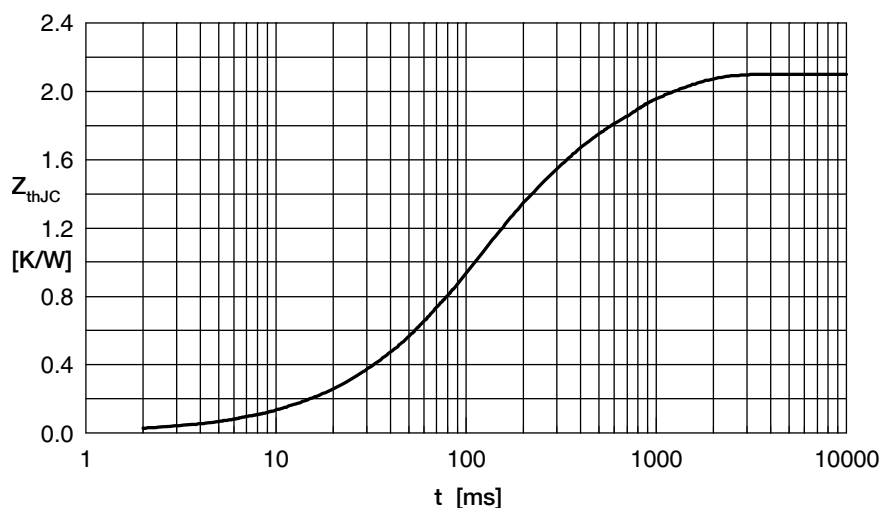


Fig. 6 Transient thermal impedance junction to case

Constants for Z_{thJC} calculation:

i	R_{thi} (K/W)	t_i (s)
1	1.159	0.1015
2	0.1286	0.1026
3	0.2651	0.4919
4	0.5473	0.62